

# MJ P-Channel Enhancement Mode Power MOSFET

## Description

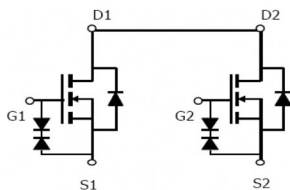
The MJ2008E uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications .It is ESD protested.

## General Features

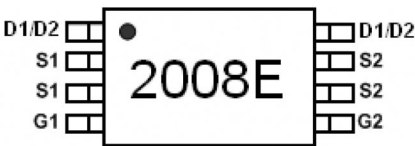
- ◆  $V_{DS} = 20V, I_D = 6A$   
 $R_{DS(ON)} < 30m\Omega @ V_{GS} = 2.5V$   
 $R_{DS(ON)} < 24m\Omega @ V_{GS} = 4.5V$   
ESD Rating: 2000V HBM
- ◆ High power and current handing capability
- ◆ Lead free product is acquired
- ◆ Surface Mount Package

## Application

- ◆ PWM application
- ◆ Load switch



Schematic diagram



Marking and pin Assignment



TSSOP-8 top view

## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2008E	MJ2008E	TSSOP-8	Ø330mm	12mm	3000 units

## Absolute Maximum Ratings (Tc =25 °Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	±12	V
Drain Current-Continuous	$I_D$	6	A
Pulsed Drain Current <sup>(Note 1)</sup>	$I_{DM}$	30	A
Maximum Power Dissipation	$P_D$	1.5	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

## Thermal Characteristic

Thermal Resistance,Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	83.3	°C/W
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Electrical Characteristics (T<sub>A</sub> =25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =±10V,V <sub>DS</sub> =0V	-	-	±10	nA
On Characteristics <sup>(Note 3)</sup>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	0.45	0.7	1.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	-	17	24	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =5A	-	22	30	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V,I <sub>D</sub> =6A	-	20	-	S
Dynamic Characteristics <sup>(Note 4)</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V,V <sub>GS</sub> =0V, F=1.0MHz	-	650	-	PF
Output Capacitance	C <sub>OSS</sub>		-	140	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	60	-	PF
Switching Characteristics <sup>(Note 4)</sup>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V,R <sub>L</sub> =1.5Ω V <sub>GS</sub> =5V,R <sub>GEN</sub> =3Ω	-	0.5	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	1	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	12	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V,I <sub>D</sub> =6A, V <sub>GS</sub> =4.5V	-	8	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	2.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <sup>(Note 3)</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =1A	-	-	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	I <sub>S</sub>		-	-	6	A

Notes:

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② Surface Mounted on FR4 Board, t ≤ 10 sec.
- ③ Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
- ④ Guaranteed by design, not subject to production

# Typical Electrical and Thermal Characteristics

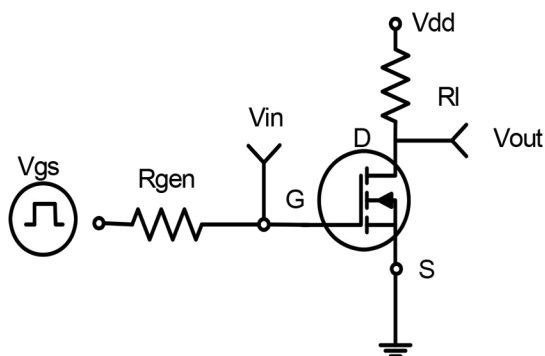


Figure 1 Switching Test Circuit

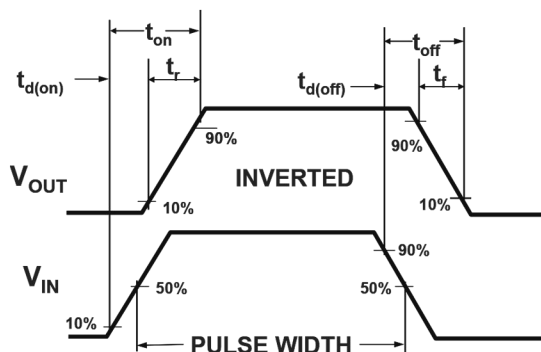


Figure 2 Switching Waveforms

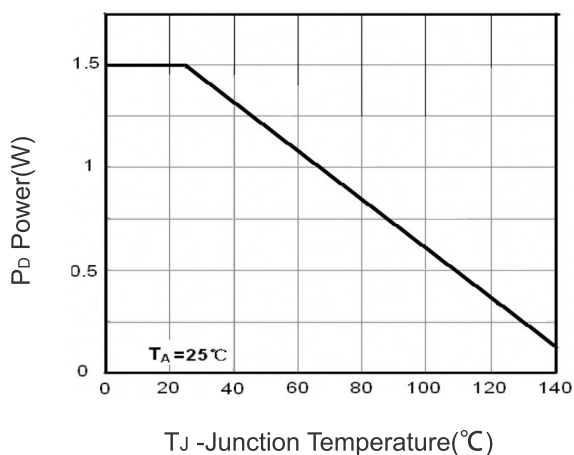


Figure 3 Power Dissipation

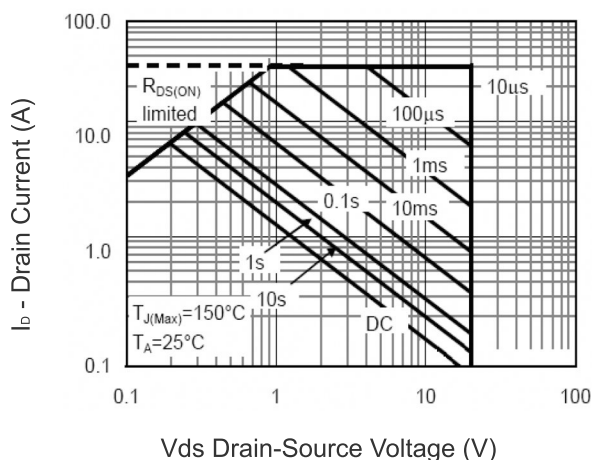


Figure 4 Safe Operation Area

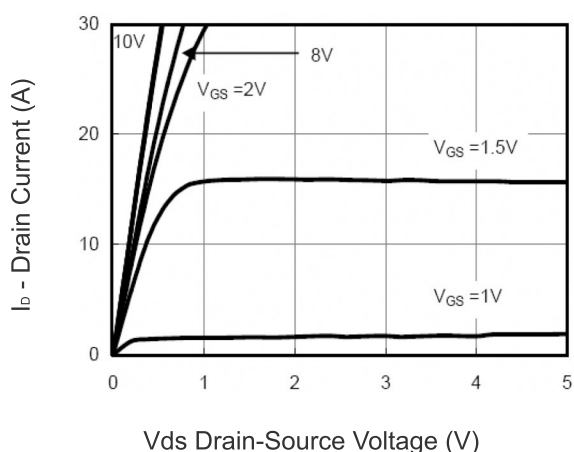


Figure 5 Output Characteristics

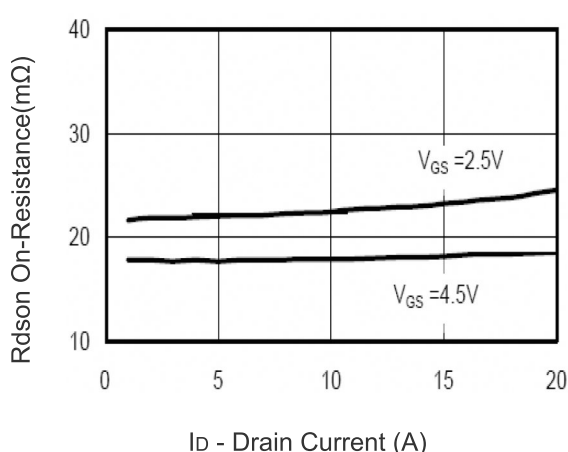
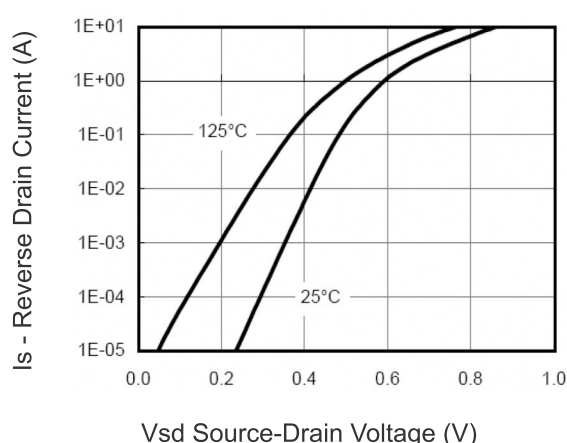
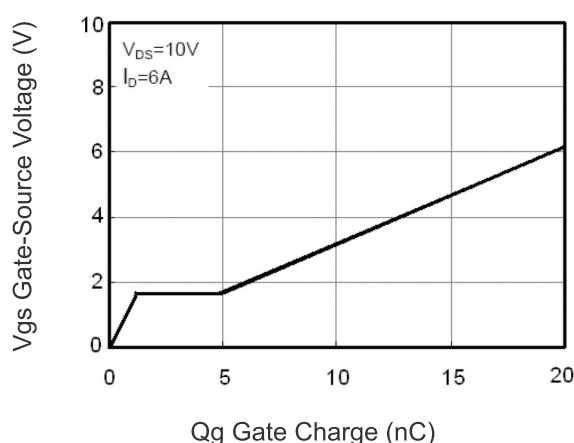
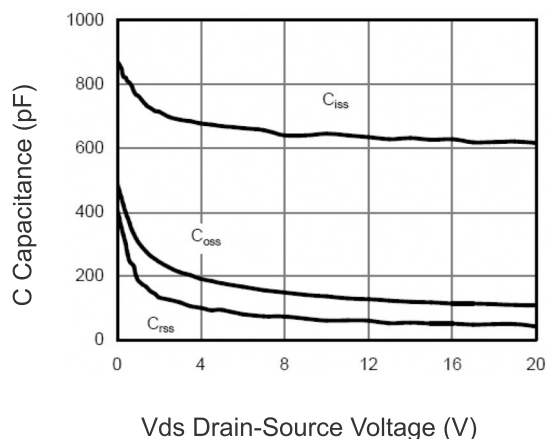
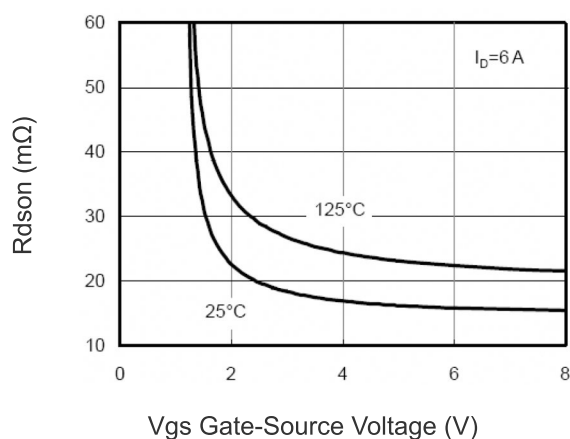
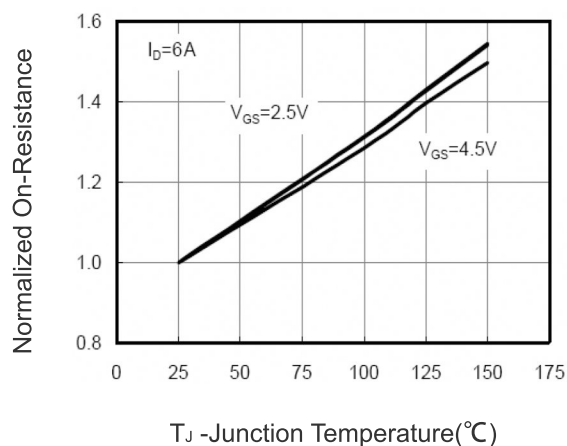
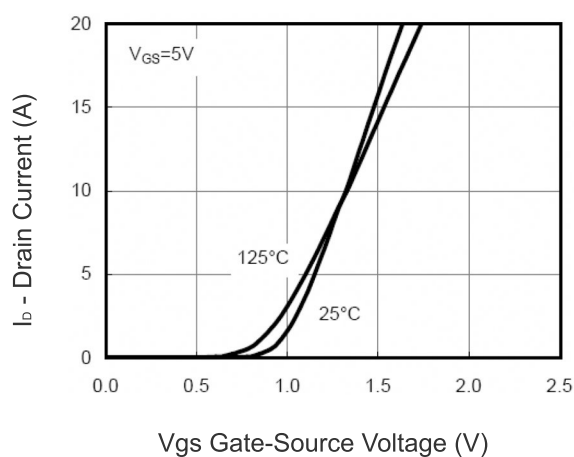


Figure 6 Drain-Source On-Resistance



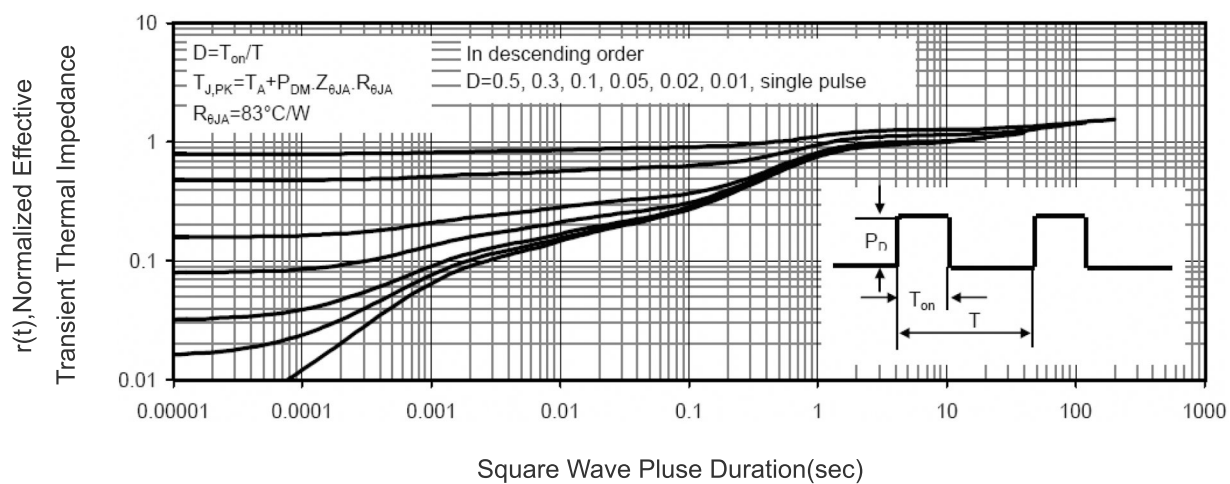
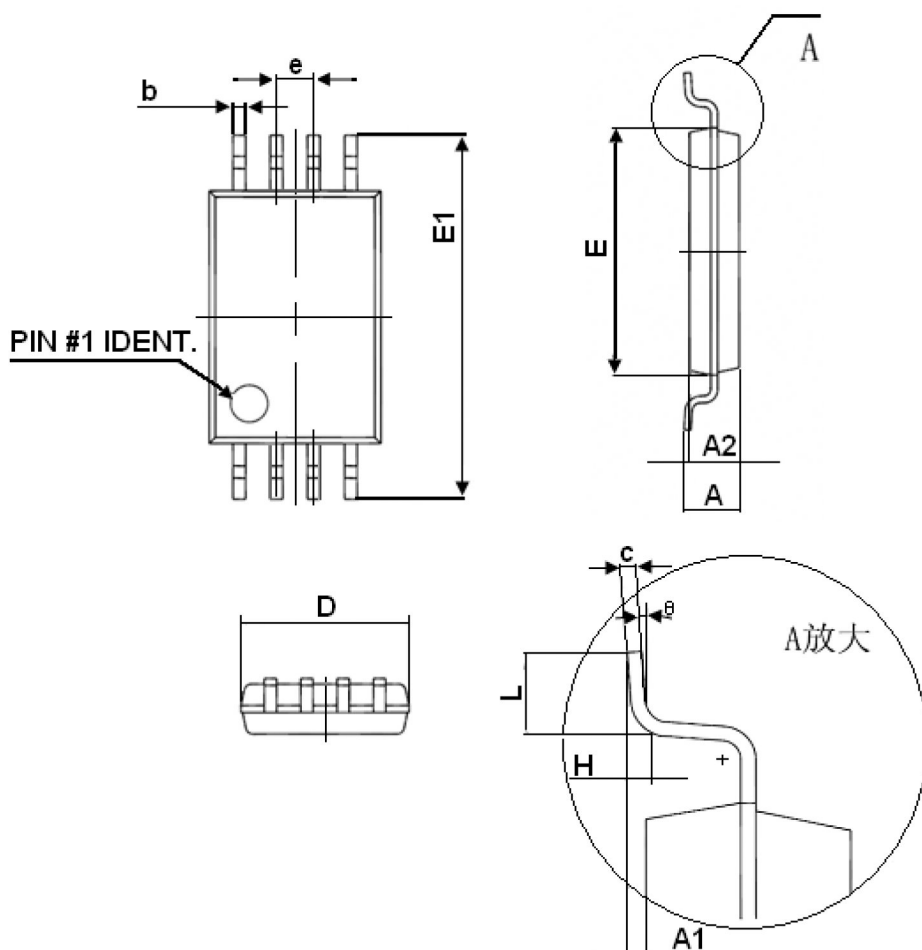


Figure 13 Normalized Maximum Transient Thermal Impedance

## Tssop-8 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
D	2.900	3.100
E	4.300	4.500
b	0.190	0.300
c	0.090	0.200
E1	6.250	6.550
A		1.100
A2	0.800	1.000
A1	0.020	0.150
e	0.65(BSC)	
L	0.500	0.700
H	0.25(TYP)	
θ	1°	7°

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